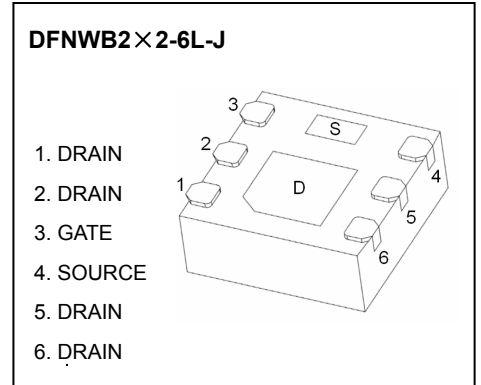


DFNWB2*2-6L-J Plastic-Encapsulate MOSFETS

CJM1216 P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-12V	21mΩ@-4.5V	-16A
	27mΩ@-2.5V	



DESCRIPTION

The CJM1216 uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge and operation with low gate voltage.

This device is suitable for use as a load switching application and a wide variety of other applications.

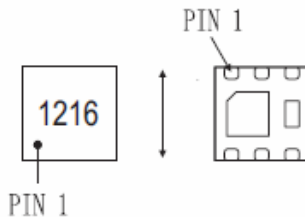
FEATURES

- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

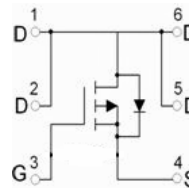
APPLICATIONS

- PWM application
- Load switch
- Battery charge in cellular handset

.....A5F?B:



Equivalent Circuit



Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-12	V
Gate-Source Voltage	V_{GS}	±8	
Drain Current-Continuous	I_D	-16	A
Drain Current-Pulsed (note 1)	I_{DM}	-65	
Power Dissipation (note 2, $T_a=25^{\circ}C$)	P_D	2.5	W
Maximum Power Dissipation (note 3, $T_c=25^{\circ}C$)		18	
Thermal Resistance from Junction to Ambient (note 4)	$R_{\theta JA}$	50	$^{\circ}C/W$
Thermal Resistance from Junction to Case (note 4)	$R_{\theta JC}$	6.9	
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 ~ +150	

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

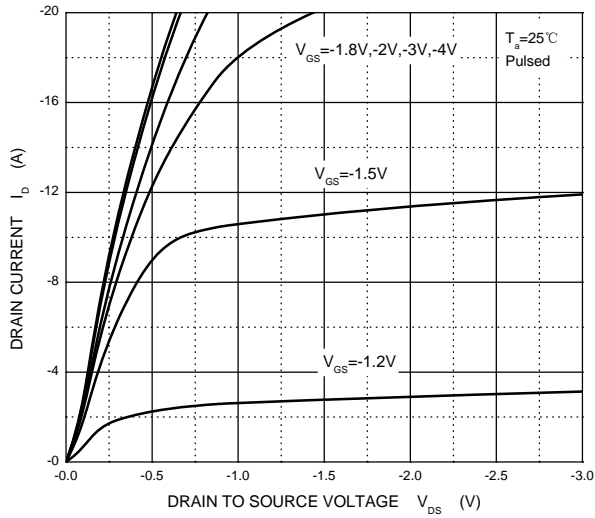
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-12			V
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0V$			-1	μA
On Characteristics (note 5)						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -6.7A$			21	m Ω
		$V_{GS} = -2.5V, I_D = -6.2A$			27	
Forward Transconductance	g_{fs}	$V_{DS} = -10V, I_D = -6.7A$		40		S
Dynamic Characteristics (note 6)						
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		2700		pF
Output Capacitance	C_{oss}			680		
Reverse Transfer Capacitance	C_{rss}			590		
Total Gate Charge	Q_g	$V_{DS} = -6V, V_{GS} = -8V, I_D = -10A$		60	100	nC
				35	48	
Gate-Source Charge	Q_{gs}	$V_{DS} = -6V, V_{GS} = -4.5V, I_D = -10A$		5		
Gate-Drain Charge	Q_{gd}			10		
Drain-Source Diode Characteristics						
Diode Forward Current (note 5)	I_S				-16	A
Diode Forward Voltage (note 4)	V_{SD}	$V_{GS} = 0V, I_{SD} = -8A$			-1.2	V

Notes:

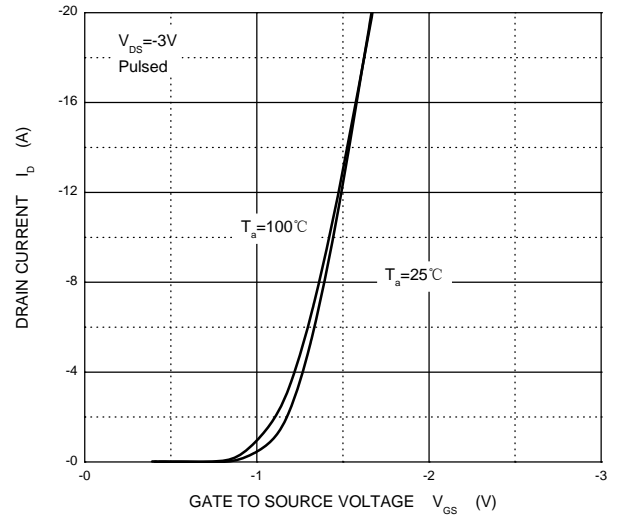
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at $T_a=25^\circ\text{C}$.
3. This test is performed with infinite heat sink at $T_c=25^\circ\text{C}$.
4. Surface mounted on FR4 board, $t \leq 10S$.
5. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
6. Guaranteed by design, not subject to production testing.

Typical Characteristics

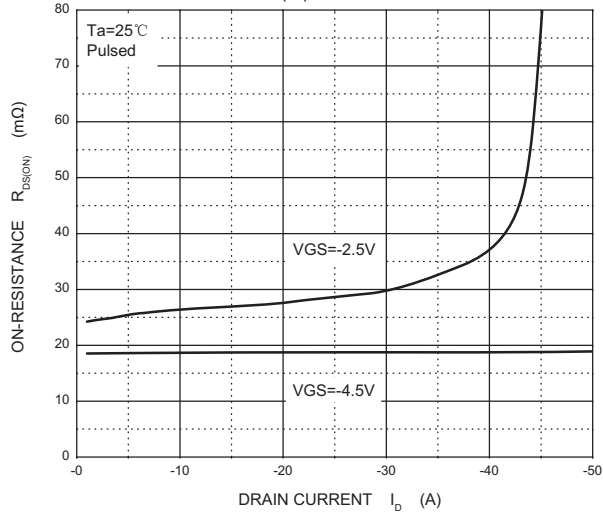
Output Characteristics



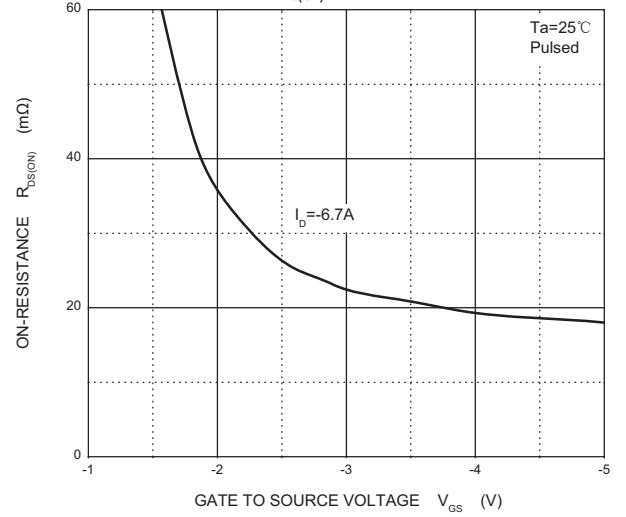
Transfer Characteristics



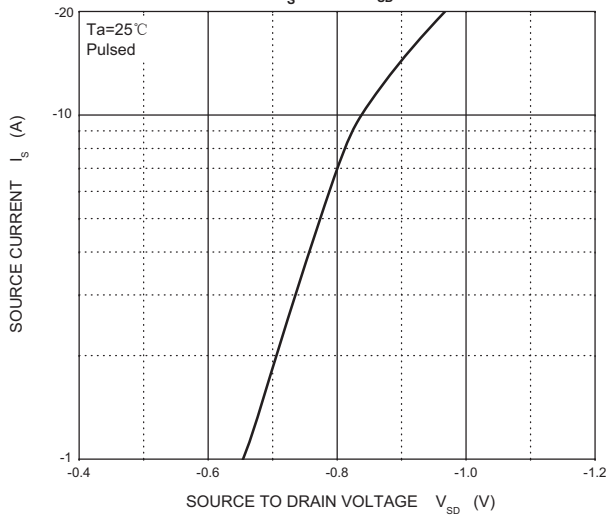
$R_{DS(ON)}$ — I_D



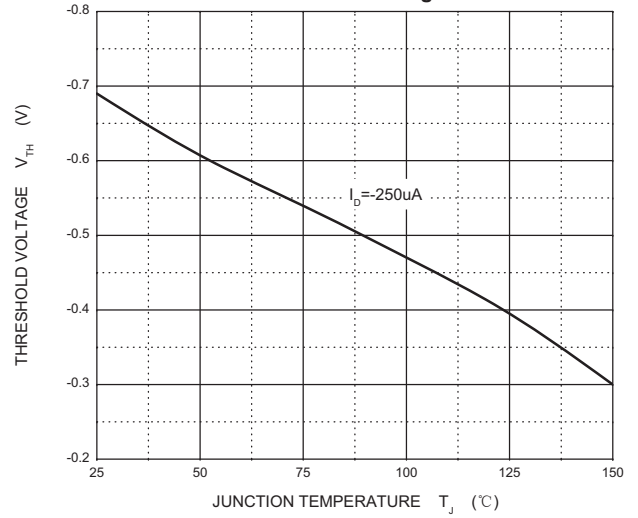
$R_{DS(ON)}$ — V_{GS}



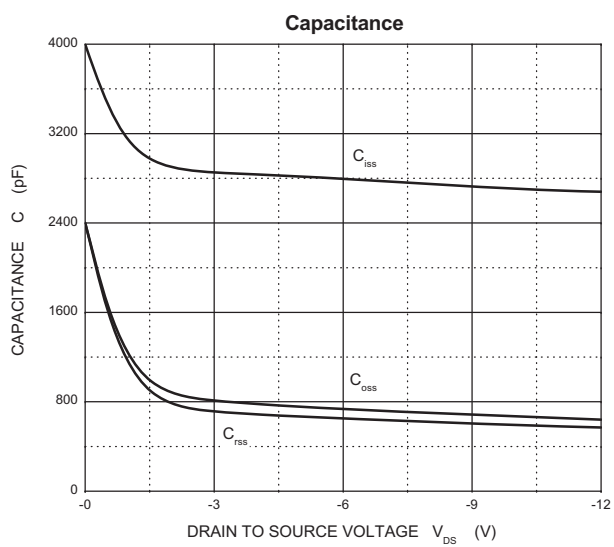
I_S — V_{SD}



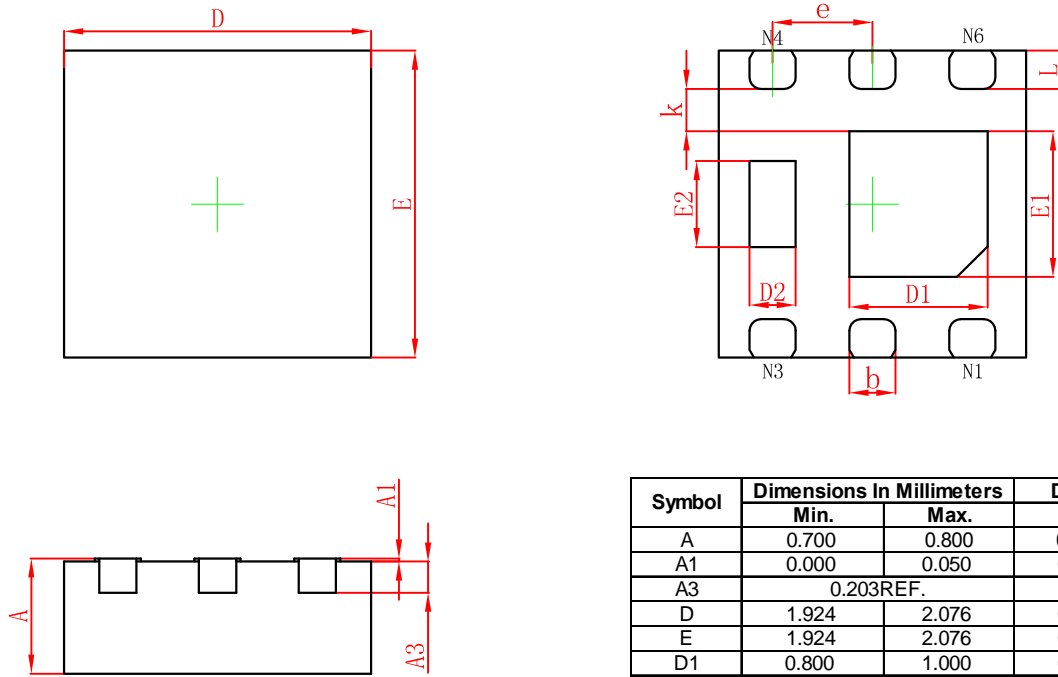
Threshold Voltage



Typical Characteristics

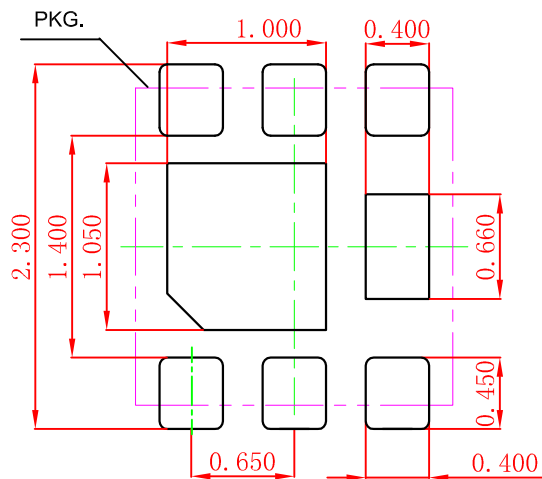


DFNWB2X2-6L-J Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.032
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

DFNWB2X2-6L-J Suggested Pad Layout



Note:

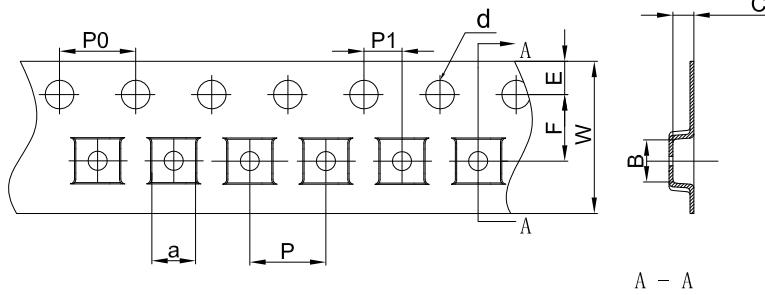
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.050 mm.
3. The pad layout is for reference purposes only.

NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

DFNWB2X2-6L Tape and Reel

DFNWB2×2-6L Embossed Carrier Tape



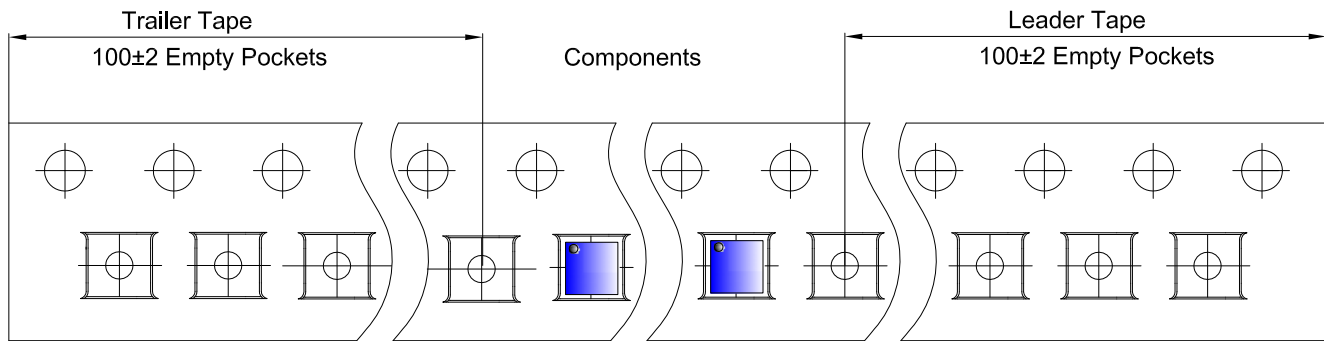
Packaging Description:

DFNWB2×2-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

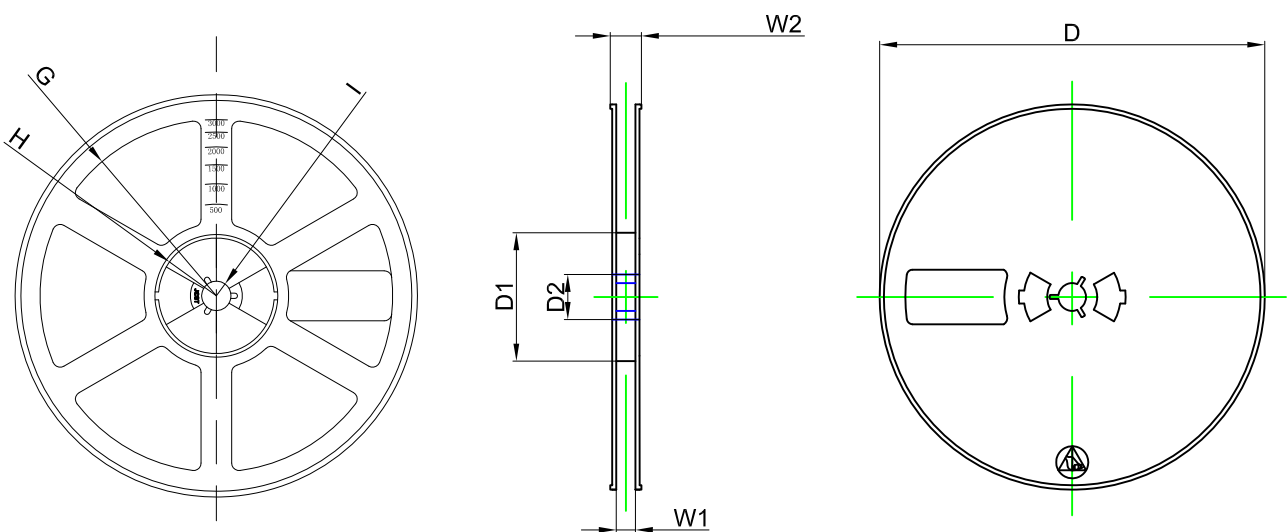
Dimensions are in millimeter

Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFNWB2×2-6L	2.30	2.30	1.10	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

DFNWB2×2-6L Tape Leader and Trailer



DFNWB2×2-6L Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	